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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/469,190	12/21/1999	KATSUHIKO HIEDA	04329.2210	4681
22852	7590 03/11/2003			
FINNEGAN, HENDERSON, FARABOW, GARRETT &			EXAMINER	
DUNNER LLI 1300 I STREE		VU, HUNG K		
WASHINGTON, DC 20006			ART UNIT	PAPER NUMBER
			2811	
			DATE MAILED: 03/11/2003	

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)			
Office Action Summary		09/469,190	HIEDA ET AL.			
	omee Action Summary	Examin r	Art Unit			
	The MAII INC DATE of this communication on	Hung K. Vu	2811			
Period fo	The MAILING DATE of this communication apported to the second section apports.	bears In the cover sheet with the	e correspondence address			
THE - Exte after - If the - If NC - Failu - Any I	ORTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. msions of time may be available under the provisions of 37 CFR 1.1 SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a repl period for reply is specified above, the maximum statutory period re to reply within the set or extended period for reply will, by statute eply received by the Office later than three months after the mailing and patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however, may a reply be by within the statutory minimum of thirty (30) dwill apply and will expire SIX (6) MONTHS from the application to become ABANDOI	timely filed lays will be considered timely. om the mailing date of this communication. NED (35 U.S.C. § 133).			
1)🖾	Responsive to communication(s) filed on 23	December 2002				
2a)⊠	This action is FINAL. 2b) The	nis action is non-final.				
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213. Disposition of Claims						
4)⊠	Claim(s) <u>1-10,15 and 17-30</u> is/are pending in	the application.				
	4a) Of the above claim(s) 1-10,15,17,18 and 20-30 is/are withdrawn from consideration.					
5)	Claim(s) is/are allowed.					
6)⊠	Claim(s) 19 is/are rejected.					
7)	7) Claim(s) is/are objected to.					
8)[8) Claim(s) are subject to restriction and/or election requirement.					
Applicati	on Papers					
, 9) <u> </u>	The specification is objected to by the Examine	۲.				
10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
11) \boxtimes The proposed drawing correction filed on <u>23 December 2002</u> is: a) \boxtimes approved b) \square disapproved by the Examiner						
If approved, corrected drawings are required in reply to this Office action.						
12)	The oath or declaration is objected to by the Ex	aminer.				
Priority u	ınder 35 U.S.C. §§ 119 and 120					
13)	Acknowledgment is made of a claim for foreign	n priority under 35 U.S.C. § 119	(a)-(d) or (f).			
a) ☐ All b) ☐ Some * c) ☐ None of:						
	1. Certified copies of the priority document	s have been received.				
	2. Certified copies of the priority document	s have been received in Applica	ation No			
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
14) 🗌 A	cknowledgment is made of a claim for domesti	c priority under 35 U.S.C. § 119	(e) (to a provisional application).			
)					
Attachment	t(s)					
2) Notic 3) Inform	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Informa	ary (PTO-413) Paper No(s) I Patent Application (PTO-152)			
J.S. Patent and To PTO-326 (Re		ction Summary	Part of Paper No 20			

Art Unit: 2811

DETAILED ACTION

Claim Rejections - 35 USC § 112

1. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

Claim 19 is rejected under 35 U.S.C. 112, first paragraph, as containing subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. The limitation (a lower electrode having a side and upper surface, wherein a surface area of the side being larger than a surface area of the upper surface) is not supported by the original specification and/or drawings.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claim 19, insofar as in compliance with 35 USC 112, is rejected under 35 U.S.C. 102(b) as being anticipated by Kashihara et al. (PN 5,567,964, of record).

Kashihara et al. discloses, as shown in Figure 14, a semiconductor device comprising,

a semiconductor substrate (31);

Application/Control Number: 09/469,190

Art Unit: 2811

a conductive plug (43a) formed on the semiconductor substrate;

a lower electrode (1) formed in contact with the conductor plug and having a side and upper surface;

a capacitor insulating film (11d) formed on a side of the lower electrode;

an upper electrode (5) formed above the lower electrode via the capacitor insulating film,

the capacitor insulating film (11d) being formed above a top surface of the lower

electrode via a second insulating film (3) different from the capacitor insulating film (11d). Note

Col. 17, lines 29-46 of Kashihara et al..

Response to Arguments

3. Applicants' arguments filed 12/23/02 have been fully considered but they are not persuasive.

It is argued, at pages 2-3 and 5 of the Remarks, that the specification, p. 32, lines 25 through page 33, line 8, describes the claimed invention. This argument is not convincing because there is nothing in those page mentions about the surface area of the side being larger than a surface area of the upper surface.

It is argued, at page 4 of the Remarks, that Kashihara et al. does not disclose the lower electrode having side and upper surfaces, a surface area of the side being larger than a surface area of the upper surface. This argument is not convincing because the limitation (a surface area of the side being larger than a surface area of the upper surface) is not support by the specification and/or drawings.

Application/Control Number: 09/469,190

Art Unit: 2811

It is argued, at pages 4-6 of the Remarks, that Kashihara et al. does not disclose the capacitor insulating layer being formed above a top surface of the lower electrode layer 1 via a second insulating film different from the capacitor insulating film. This argument is not convincing because Kashihara et al. teaches, as shown in Figure 14, the capacitor insulating layer (11d) being formed above a top surface of the lower electrode layer (1) via a second insulating film (3) different from the capacitor insulating film (11d). Note that Kashihara et al. teaches, at Col. 17, lines 29-46, the material of film (11d) comprising silicon nitride film, a silicon oxide film, ZrO₂, TiO₂ or Ta₂O₅. Also, at Col. 14, lines 57-59, Kashihara et al. teaches the material of film (3) comprising BST, ST or PZT. Also note that any insulating film forms between the lower electrode layer and the upper electrode layer is considered as the capacitor insulating film.

Conclusion

4. THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event,

Application/Control Number: 09/469,190

Art Unit: 2811

however, will the statutory period for reply expire later than SIX MONTHS from the mailing

date of this final action.

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Hung K. Vu whose telephone number is (703) 308-4079. The

examiner can normally be reached on Mon-Thurs 7:00-5:30, Eastern Time.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Tom Thomas can be reached on (703) 308-2772. The fax phone numbers for the

organization where this application or proceeding is assigned are (703) 308-7722 for regular

communications and (703) 308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is (703) 308-0956.

Vu

March 5, 2003

TOM THOMAS
SUPERVISORY PATENT EXAMINER

Page 5

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